

MOSFETs Silicon P-Channel MOS (U-MOSVI)

SSM3J66MFV

1. Applications

· Load Switches

2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 1.2-V drive
- (3) Low drain-source on-resistance
 - $: R_{DS(ON)} = 390 \text{ m}\Omega \text{ (max) } (@V_{GS} = -4.5 \text{ V})$

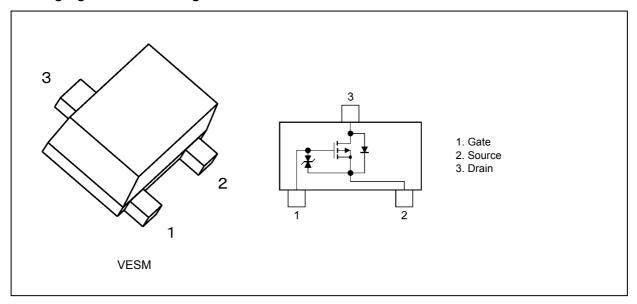
 $R_{\rm DS(ON)} = 480 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -2.5 \ {\rm V})$

 $R_{DS(ON)} = 660 \text{ m}\Omega \text{ (max) (@V_{GS} = -1.8 V)}$

 $R_{\rm DS(ON)} = 900 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -1.5 \ {\rm V})$

 $R_{DS(ON)} = 4000 \text{ m}\Omega \text{ (max) (@V_{GS} = -1.2 V)}$

3. Packaging and Pin Configuration



4. Orderable part number

Orderable part number	AEC-Q101 No			
SSM3J66MFV,L3F	_		General Use	
SSM3J66MFV,L3XGF	YES	(Note 1)	Unintended Use	(Note 1)
SSM3J66MFV,L3XHF	YES		Automotive Use	

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production



5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				V _{DSS}	-20	V
Gate-source voltage				V_{GSS}	-8/+6	
Drain current (DC)			(Note 1)	I _D	-0.8	Α
Drain current (pulsed)			(Note 1), (Note 2)	I _{DP}	-1.6	
Power dissipation			(Note 3)	P_{D}	150	mW
Power dissipation			(Note 4)	P_{D}	500	
Power dissipation		(t < 5 s)	(Note 4)	P_D	800	
Channel temperature				T _{ch}	150	°C
Storage temperature				T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW) \leq 1 ms, duty < 1 %
- Note 3: Device mounted on an FR4 board.(25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 0.585 mm²)
- Note 4: Device mounted on an FR4 board.(25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm²)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



6. Electrical Characteristics

6.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{DS} = 0 V, V _{GS} = -8/+6 V	_	_	±1	μА
Drain cut-off current		I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V	_	_	-1	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = -1 mA, V _{GS} = 0 V	-20	_	_	V
Drain-source breakdown voltage	(Note 1)	V _{(BR)DSX}	I _D = -1 mA, V _{GS} = 5 V	-15	_	_	
Gate threshold voltage	(Note 2)	V_{th}	V _{DS} = -3 V, I _D = -1 mA	-0.3	_	-1.0	
Drain-source on-resistance	(Note 3)	R _{DS(ON)}	I _D = -10 mA, V _{GS} = -1.2 V	_	770	4000	mΩ
			I _D = -100 mA, V _{GS} = -1.5 V	_	560	900	
			I _D = -200 mA, V _{GS} = -1.8 V	_	470	660	
			I _D = -500 mA, V _{GS} = -2.5 V	_	380	480	
			I _D = -800 mA, V _{GS} = -4.5 V	_	310	390	
Forward transfer admittance	(Note 3)	Y _{fs}	$V_{DS} = -3 \text{ V}, I_{D} = -100 \text{ mA}$	0.5	1.0	_	S

- Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.
- Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (-1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.

 Take this into consideration when using the device.

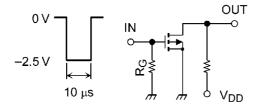
Note 3: Pulse measurement.

6.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V,	_	100	_	pF
Reverse transfer capacitance		C _{rss}	f = 1 MHz	_	10		
Output capacitance		C _{oss}		_	16	_	
Switching time (turn-on time)	(Note 1)		$V_{DD} = -10 \text{ V}, I_D = -200 \text{ mA},$	_	8	_	ns
Switching time (turn-off time)	(Note 1)	t _{off}	V_{GS} = 0 to -2.5 V, R_{G} = 50 Ω	_	26		

Note 1: Duty \leq 1 %, input t_r , t_f < 5 ns, Common source

6.3. Switching Time Test Circuit



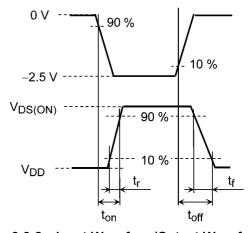


Fig. 6.3.1 Test Circuit of Switching Time

Fig. 6.3.2 Input Waveform/Output Waveform



6.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	9	V_{DD} = -10 V, I_D = -800 mA,	_	1.6	_	nC
Gate-source charge 1	Q _{gs1}	V _{GS} = -4.5 V	_	0.2	_	
Gate-drain charge	Q _{gd}		_	0.4	_	

6.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	I_D = 800 mA, V_{GS} = 0 V		0.9	1.2	٧

Note 1: Pulse measurement.

7. Marking

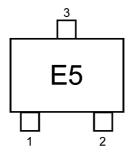


Fig. 7.1 Marking



8. Characteristics Curves (Note)

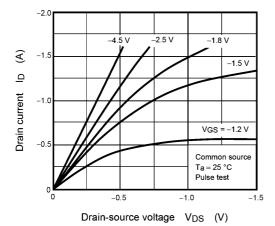


Fig. 8.1 I_D - V_{DS}

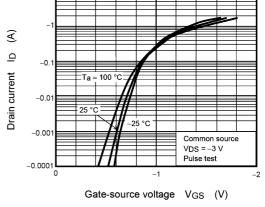


Fig. 8.2 I_D - V_{GS}

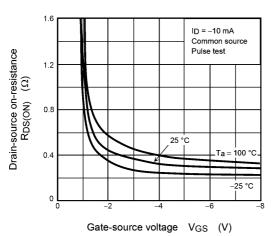


Fig. 8.3 R_{DS(ON)} - V_{GS}

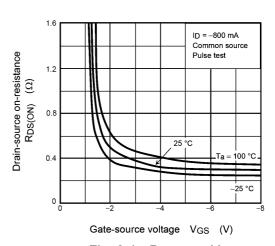


Fig. 8.4 R_{DS(ON)} - V_{GS}

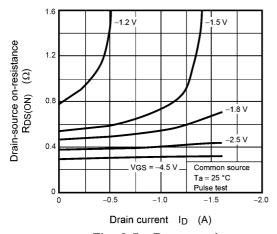


Fig. 8.5 R_{DS(ON)} - I_D

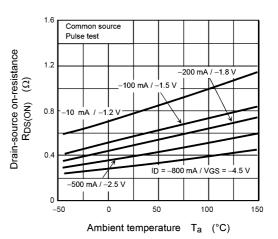


Fig. 8.6 R_{DS(ON)} - T_a

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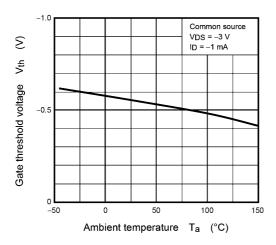


Fig. 8.7 V_{th} - T_a

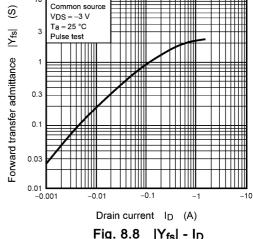


Fig. 8.8 |Y_{fs}| - I_D

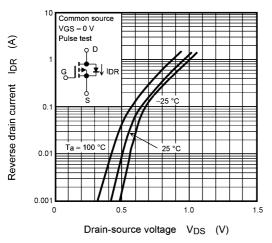


Fig. 8.9 I_{DR} - V_{DS}

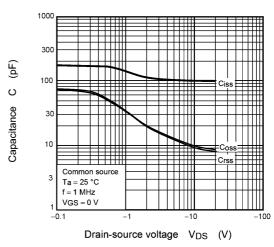


Fig. 8.10 C - V_{DS}

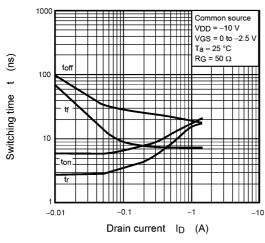


Fig. 8.11 t - I_D

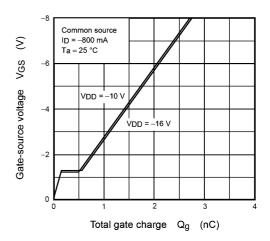
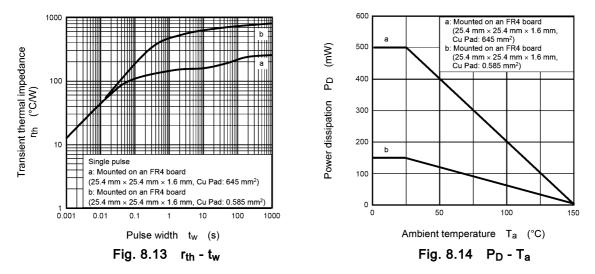


Fig. 8.12 Dynamic Input Characteristics



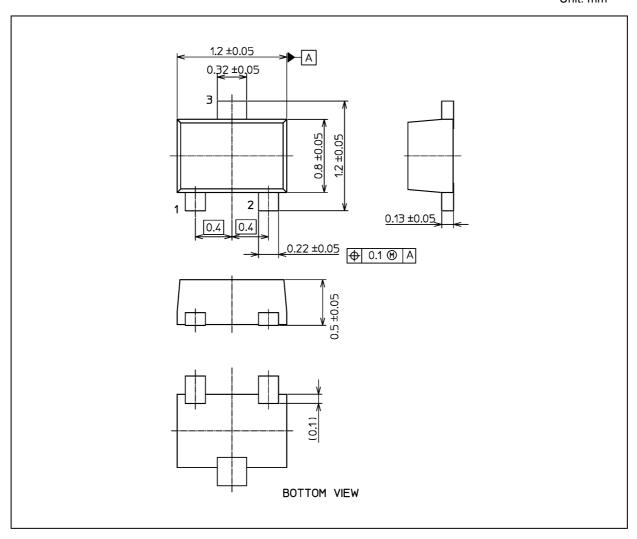


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.5 mg (typ.)

	Package Name(s)
TOSHIBA: 1-1Q1S	
Nickname: VESM	



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